Quad 3-State Noninverting Buffer with LSTTL Compatible Inputs

High-Performance Silicon-Gate CMOS

The MC74HCT125A is identical in pinout to the LS125. The device inputs are compatible with standard CMOS and LSTTL outputs.

The MC74HCT125A noninverting buffer is designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. The devices have four separate output enables that are active-low.

Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the JEDEC Standard No. 7A Requirements
- Chip Complexity: 72 FETs or 18 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb–Free Devices

PIN ASSIGNMENT

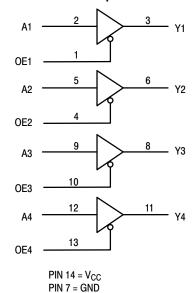
| 0E1 [| 1 ● | | □ v _{cc} |
|-------|-----|----|-------------------|
| A1 [| 2 | 13 |] OE4 |
| Y1 [| 3 | 12 |] A4 |
| OE2 | 4 | 11 |] Y4 |
| A2 [| 5 | 10 | 0E3 |
| Y2 [| 6 | 9 |] A3 |
| GND [| 7 | 8 |] Y3 |
| | | | , |

FUNCTION TABLE

| HCT125A | | | | |
|---------------|----|---|--|--|
| Inputs Output | | | | |
| Α | OE | Υ | | |
| Н | L | Н | | |
| L | L | L | | |
| Х | Н | Z | | |

LOGIC DIAGRAM

Active-Low Output Enables





ON Semiconductor®

http://onsemi.com

MARKING DIAGRAMS



SOIC-14 D SUFFIX CASE 751A





TSSOP-14 DT SUFFIX CASE 948G



A = Assembly Location

L, WL = Wafer Lot Y, YY = Year

W, WW = Work Week
G = Pb-Free Package
• Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|------------------|---|--------------------------|------|
| V _{CC} | DC Supply Voltage (Referenced to GND) | - 0.5 to + 7.0 | V |
| V _{in} | DC Input Voltage (Referenced to GND) | -0.5 to $V_{CC} + 0.5$ | V |
| V _{out} | DC Output Voltage (Referenced to GND) | -0.5 to $V_{CC} + 0.5$ | V |
| I _{in} | DC Input Current, per Pin | ± 20 | mA |
| I _{out} | DC Output Current, per Pin | ± 35 | mA |
| I _{CC} | DC Supply Current, V _{CC} and GND Pins | ± 75 | mA |
| P _D | Power Dissipation in Still Air SOIC Package† TSSOP Package† | 500 450 | mW |
| T _{stg} | Storage Temperature | - 65 to + 150 | °C |
| TL | Lead Temperature, 1 mm from Case for 10 Seconds (SOIC or TSSOP Package) | 260 | °C |

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or $V_{\rm CC}$). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — SOIC Package: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | | Min | Max | Unit |
|------------------------------------|--|--|-----------------|--------------------|------|
| V _{CC} | DC Supply Voltage (Referenced to GND) | | 2.0 | 6.0 | V |
| V _{in} , V _{out} | DC Input Voltage, Output Voltage (Referenced to GND) | 0 | V _{CC} | V | |
| T _A | Operating Temperature, All Package Type | - 55 | + 125 | °C | |
| t _r , t _f | (Figure 1) | $V_{CC} = 2.0 \text{ V}$ $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$ | 0 0 0 | 1000 500 400 | ns |

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

| | | | | Guaranteed Limit | | | |
|-----------------|--|---|----------------------|--------------------|--------------------|-------------------|------|
| Symbol | Parameter | Test Conditions | V _{CC} V | – 55 to 25°C | ≤ 85°C | ≤ 125°C | Unit |
| V _{IH} | Minimum High-Level Input Voltage | $V_{\text{out}} = V_{\text{CC}} - 0.1 \text{ V}$ $ I_{\text{out}} \le 20 \mu\text{A}$ | 4.5 to 5.5 | 2.0 | 2.0 | 2.0 | V |
| V _{IL} | Maximum Low–Level Input Voltage | $V_{out} = 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$ | 4.5 to 5.5 | 0.8 | 0.8 | 0.8 | V |
| V _{OH} | Minimum High-Level Output Voltage | $V_{in} = V_{IH}$ $ I_{out} \le 20 \mu A$ | 4.5 5.5 4.5 | 4.4 5.4 3.98 | 4.4 5.4 | 4.4 5.4 3.7 | V |
| V _{OL} | Maximum Low–Level Output Voltage | $\begin{aligned} &V_{in} = V_{IH} & & I_{out} \leq 6.0 \text{ mA} \\ &V_{in} = V_{IL} & & \\ & I_{out} \leq 20 \mu\text{A} \end{aligned}$ | 4.5 5.5 | 0.1 0.1 | 3.84 0.1 0.1 | 0.1 0.1 | V |
| l _{in} | Maximum Input Leakage Current | $V_{in} = V_{IL}$ $ I_{out} \le 6.0 \text{ mA}$ $V_{in} = V_{CC} \text{ or GND}$ | 4.5 5.5 | 0.26 ± 0.1 | 0.33 ± 1.0 | 0.4 ± 1.0 | μΑ |
| I _{OZ} | Maximum Three–State Leakage Current | Output in High-Impedance State $V_{in} = V_{IL}$ or V_{IH} $V_{out} = V_{CC}$ or GND | 5.5 | ± 0.5 | ± 5.0 | ± 10 | μΑ |
| Icc | Maximum Quiescent Supply Current (per Package) | $V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$ | 5.5 | 4.0 | 40 | 160 | μΑ |

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6.0 ns, V_{CC} = 5.0 V \pm 10%)

| | | | Gu | aranteed Li | mit | |
|--|---|-----------------|-----------------|------------------------|----------------------|------|
| Symbol | Parameter | v _{cc} | – 55 to 25°C | ≤ 85°C | ≤ 125°C | Unit |
| t _{PLH} , t _{PHL} | Maximum Propagation Delay, Input A to Output Y (Figures 1 and 3) | 5.0 | 18 | 23 | 27 | ns |
| t _{PLZ} , t _{PHZ} | Maximum Propagation Delay, Output Enable to Y (Figures 2 and 4) | 5.0 | 24 | 30 | 36 | ns |
| t _{PZL} , t _{PZH} | Maximum Propagation Delay, Output Enable to Y (Figures 2 and 4) | 5.0 | 18 | 23 | 27 | ns |
| t _{TLH} , t _{THL} | Maximum Output Transition Time, Any Output (Figures 1 and 3) | 5.0 | 12 | 15 | 18 | ns |
| C _{in} | Maximum Input Capacitance | - | 10 | 10 | 10 | pF |
| C _{out} | Maximum 3-State Output Capacitance (Output in High-Impedance State) | - | 15 | 15 | 15 | pF |
| | | | Typical | @ 25°C, V _C | _C = 5.0 V | |
| Con | Power Dissination Canacitance (Per Buffer)* | | | 30 | | nЕ |

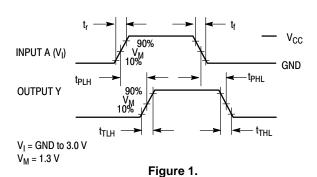
ORDERING INFORMATION

| Device | Package | Shipping [†] |
|-------------------|-----------------------|-----------------------|
| MC74HCT125ADG | | 55 Units / Rail |
| MC74HCT125ADR2G | SOIC-14 (Pb-Free) | 2500 / Tape & Reel |
| NLV74HCT125ADR2G* | | 2500 / Tape & Reel |
| MC74HCT125ADTG | | 96 Units / Rail |
| MC74HCT125ADTR2G | TSSOP-14 (Pb-Free) | 2500 / Tape & Reel |
| NLVHCT125ADTR2G* | | 2500 / Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

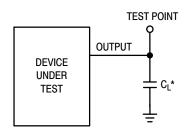
^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

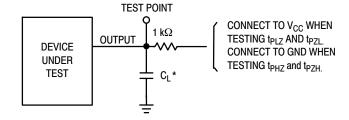
SWITCHING WAVEFORMS



 ν_{CC} OE (V_I) V_{M} GND HIGH IMPEDANCE **OUTPUT Y** 10% V_{OL} t_{PZH} t_{PHZ} - V_OH 90% **OUTPUT Y** HIGH **IMPEDANCE**

Figure 2.



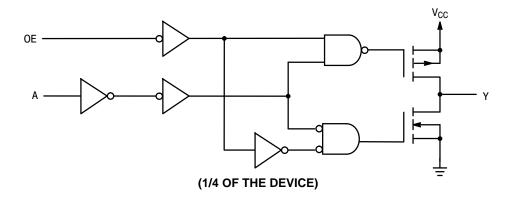


*Includes all probe and jig capacitance

*Includes all probe and jig capacitance



Figure 4. Test Circuit

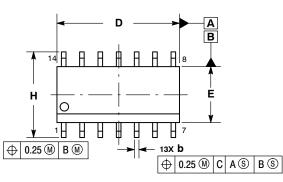


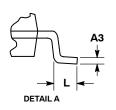


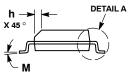
△ 0.10

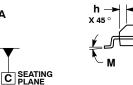
SOIC-14 NB CASE 751A-03 ISSUE L

DATE 03 FEB 2016





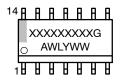




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
 - ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 - DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

| | MILLIMETERS | | INCHES | |
|-----|-------------|------|--------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 1.35 | 1.75 | 0.054 | 0.068 |
| A1 | 0.10 | 0.25 | 0.004 | 0.010 |
| АЗ | 0.19 | 0.25 | 0.008 | 0.010 |
| b | 0.35 | 0.49 | 0.014 | 0.019 |
| D | 8.55 | 8.75 | 0.337 | 0.344 |
| Е | 3.80 | 4.00 | 0.150 | 0.157 |
| е | 1.27 BSC | | 0.050 | BSC |
| Н | 5.80 | 6.20 | 0.228 | 0.244 |
| h | 0.25 | 0.50 | 0.010 | 0.019 |
| L | 0.40 | 1.25 | 0.016 | 0.049 |
| M | 0 ° | 7° | 0 ° | 7° |

GENERIC MARKING DIAGRAM*

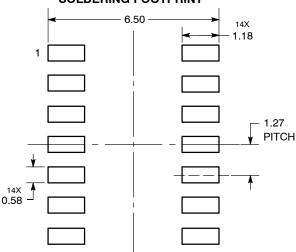


XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator. "G" or microdot " ■". may or may not be present.

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

STYLES ON PAGE 2

| DOCUMENT NUMBER: | 98ASB42565B | Electronic versions are uncontrolled except when accessed directly from the Document Reposite Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. | |
|------------------|-------------|--|-------------|
| DESCRIPTION: | SOIC-14 NB | | PAGE 1 OF 2 |

ON Semiconductor and un are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

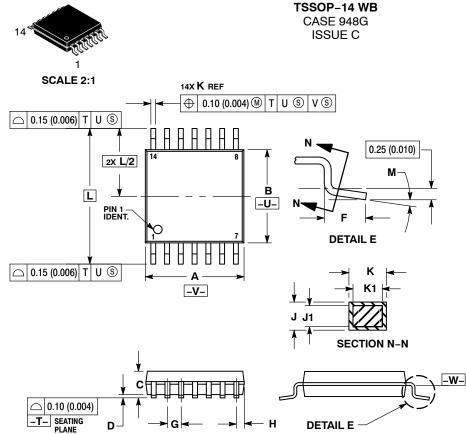
SOIC-14 CASE 751A-03 ISSUE L

DATE 03 FEB 2016

| STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE | STYLE 2: CANCELLED | STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE | STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE |
|---|---|---|---|
| STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE | STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE | STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE | STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE |

| DOCUMENT NUMBER: | 98ASB42565B | Electronic versions are uncontrolled except when accessed directly from the Document Reposite Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. | |
|------------------|-------------|---|-------------|
| DESCRIPTION: | SOIC-14 NB | | PAGE 2 OF 2 |

ON Semiconductor and IN are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.



SOLDERING FOOTPRINT

7.06

14X

1.26

DATE 17 FEB 2016

- NOTES.

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

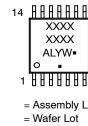
 3. DIMENSION A DOES NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

 6. TERMINAL NUMBERS ARE SHOWN FOR DEFERENCE ONLY
- REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE
 DETERMINED AT DATUM PLANE -W-.

| | MILLIMETERS | | INC | HES |
|-----|-------------|------|-----------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 4.90 | 5.10 | 0.193 | 0.200 |
| В | 4.30 | 4.50 | 0.169 | 0.177 |
| С | | 1.20 | | 0.047 |
| D | 0.05 | 0.15 | 0.002 | 0.006 |
| F | 0.50 | 0.75 | 0.020 | 0.030 |
| G | 0.65 | BSC | 0.026 | BSC |
| Н | 0.50 | 0.60 | 0.020 | 0.024 |
| J | 0.09 | 0.20 | 0.004 | 0.008 |
| J1 | 0.09 | 0.16 | 0.004 | 0.006 |
| K | 0.19 | 0.30 | 0.007 | 0.012 |
| K1 | 0.19 | 0.25 | 0.007 | 0.010 |
| L | 6.40 | BSC | 0.252 BSC | |
| М | 0 ° | 8 ° | o ° | a ° |

GENERIC MARKING DIAGRAM*



= Assembly Location

= Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

| DOCUMENT NUMBER: | 98ASH70246A | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. | |
|------------------|-------------|---|-------------|
| DESCRIPTION: | TSSOP-14 WB | | PAGE 1 OF 1 |

DIMENSIONS: MILLIMETERS

0.65

PITCH

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

14X

0.36

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer pu

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

onsemi:

MC74HCT125ADG MC74HCT125ADR2G MC74HCT125ADTG MC74HCT125ADTR2G NLV74HCT125ADR2G NLVHCT125ADTR2G